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	1.	Anticipatory Governance							
		By: Quay, Ray JOURNAL OF THE AMERICAN PLANNING ASSOCIATION Volume: 76 Issue: 4 Pages: 496-511 Article Number: PII 926306037 Published: 2010	14	16	20	7	0	72	9.00
	2.	Using Watered Landscapes to Manipulate Urban Heat Island Effects: How Much Water Will It Take to Cool Phoenix?							
		By: Gober, Patricia; Brazel, Anthony; Quay, Ray; et al. JOURNAL OF THE AMERICAN PLANNING ASSOCIATION Volume: 76 Issue: 1 Pages: 109-121 Article Number: PII 918246972 Published: 2010	5	10	13	8	0	57	7.12
	3.	A temperature dependent model for the saturation velocity in semiconductor materials							
		By: Quay, R; Moglestue, C; Palankovski, V; et al. Conference: Spring Meeting of the European-Materials-Research-Society Location: STRASBOURG, FRANCE Date: JUN 01-04, 1999 Sponsor(s): European Mat Res Soc MATERIALS SCIENCE IN SEMICONDUCTOR PROCESSING Volume: 3 Issue: 1-2 Pages: 149-155 Published: MAR 2000	5	4	5	7	0	49	2.72
	4.	High-temperature modeling of AlGaN/GaN HEMTs							
		By: Vitanov, S.; Palankovski, V.; Maroldt, S.; et al. Conference: International Semiconductor Device Research Symposium (ISDRS 2009) Location: Univ Maryland, Stamp Union, College Pk, MD Date: DEC 09-11, 2009	5	7	10	6	0	47	5.88
		SOLID-STATE ELECTRONICS Volume: 54 Issue: 10 Special Issue: SI Pages: 1105-1112 Published: OCT 2010							
	5.	Gate-Recessed AlGaN/GaN Based Enhancement-Mode High Electron Mobility Transistors for High Frequency Operation							
		By: Maroldt, Stephan; Haupt, Christian; Pletschen, Wilfried; et al. Conference: International Conference on Solid State Devices and Materials Location: Tsukuba, JAPAN Date: SEP 24-26, 2008 Sponsor(s): Tsukuba Int Congr Ctr; Japan Soc Appl Phys & Tech; IEEE Electron Devices Soc JAPANESE JOURNAL OF APPLIED PHYSICS Volume: 48 Issue: 4 Article Number: 04C083 Published: APR 2009	0	3	1	3	0	38	4.22
	0								
Ш	6.	102-GHz AllnN/GaN HEMTs on Silicon With 2.5-W/mm Output Power at 10 GHz							
		By: Sun, Haifeng; Alt, Andreas R.; Benedickter, Hansruedi; et al. IEEE ELECTRON DEVICE LETTERS Volume: 30 Issue: 8 Pages: 796-798 Published: AUG 2009	1	3	4	0	0	36	4.00
	7.	The Continuous Inverse Class-F Mode With Resistive Second- Harmonic Impedance							
		By: Carrubba, Vincenzo; Akmal, Muhammad; Quay, Ruediger; et al. IEEE TRANSACTIONS ON MICROWAVE THEORY AND TECHNIQUES Volume: 60 Issue: 6 Special Issue: SI Pages: 1928-1936 Part: 2 Published: JUN 2012	7	4	8	6	0	32	5.33
	8.	A systematic state-space approach to large-signal transistor modeling							
		By: Seelmann-Eggebert, Matthias; Merkle, Thomas; van Raay, Friedbert; et al. IEEE TRANSACTIONS ON MICROWAVE THEORY AND TECHNIQUES Volume: 55 Issue: 2 Pages: 195-206 Part: 1 Published: FEB 2007	4	1	1	0	0	30	2.73
	9.	GaN-Based Submicrometer HEMTs With Lattice-Matched InAlGaN Barrier Grown by MBE							
		By: Lim, T.; Aidam, R.; Waltereit, P.; et al. IEEE ELECTRON DEVICE LETTERS Volume: 31 Issue: 7 Pages: 671-673 Published: JUL 2010	3	4	5	1	0	28	3.50
	10.	AlGaN/GaN epitaxy and technology	1	1	1	0	0	23	2.88
		By: Waltereit, Patrick; Bronner, Wolfgang; Quay, Ruediger; et al.							

INTERNATIONAL JOURNAL OF MICROWAVE AND WIRELESS TECHNOLOGIES Volume: 2 Issue: 1 Pages: 3-11 Published: FEB 2010									
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